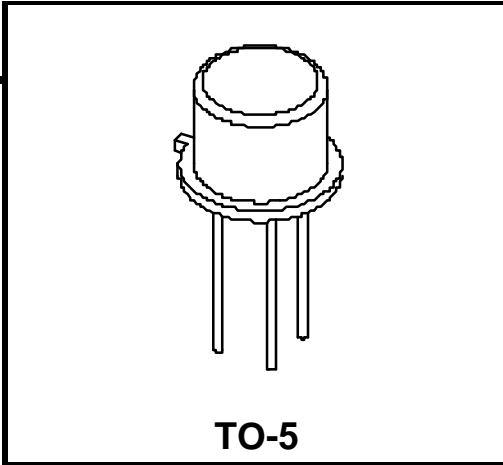


**2N3719**

**Silicon PNP  
 Power Transistors**



**APPLICATIONS:**

- High-Speed Switching
- Medium-Current Switching
- High-Frequency Amplifiers

**FEATURES:**

- Collector-Emitter Sustaining Voltage:  
 $V_{CEO(SUS)} = 40 \text{ Vdc (Min) - 2N3719}$
- DC Current Gain:  
 $h_{FE} = 25-180 @ I_C = 1.0 \text{ Adc}$
- Low Collector-Emitter Saturation Voltage:  
 $V_{CE(sat)} = 0.75 \text{ Vdc @ } I_C = 1.0 \text{ Adc}$
- High Current-Gain - Bandwidth Product:  
 $f_T = 90 \text{ MHz (Typ)}$

**DESCRIPTION:**

These power transistors are produced by PPC's DOUBLE DIFFUSED PLANAR process. This technology produces high voltage devices with excellent switching speeds, frequency response, gain linearity, saturation voltages, high current gain, and safe operating areas. They are intended for use in Commercial, Industrial, and Military power switching, amplifier, and regulator applications.

Ultrasonically bonded leads and controlled die mount techniques are utilized to further increase the SOA capability and inherent reliability of these devices. The temperature range to 200°C permits reliable operation in high ambients, and the hermetically sealed package insures maximum reliability and long life.

**ABSOLUTE MAXIMUM RATINGS:**

SYMBOL	CHARACTERISTIC	VALUE	UNITS
$V_{CEO}^*$	Collector-Emitter Voltage	40	Vdc
$V_{CB}^*$	Collector-Base Voltage	40	Vdc
$V_{EB}^*$	Emitter-Base Voltage	4.0	Vdc
$I_C^*$	Peak Collector Current	10	Adc
$I_C^*$	Continuous Collector Current	3.0	Adc
$I_B^*$	Base Current	0.5	Adc
$T_{STG}^*$	Storage Temperature	-65 to 200	°C
$T_J^*$	Operating Junction Temperature	-65 to 200	°C
$P_D^*$	Total Device Dissipation $T_C = 25^\circ\text{C}$	6.0	Watts
	Derate above 25°C	34.3	mW/°C
$P_D^*$	Total Device Dissipation $T_A = 25^\circ\text{C}$	1.0	Watts
	Derate above 25°C	5.71	mW/°C
$\theta_{JC}$	Thermal Resistance Junction to Case	29	°C/W
	Junction to Ambient	175	°C/W

\* Indicates JEDEC registered Data.

**ELECTRICAL CHARACTERISTICS:**  
**(25°C Case Temperature Unless Otherwise Noted)**

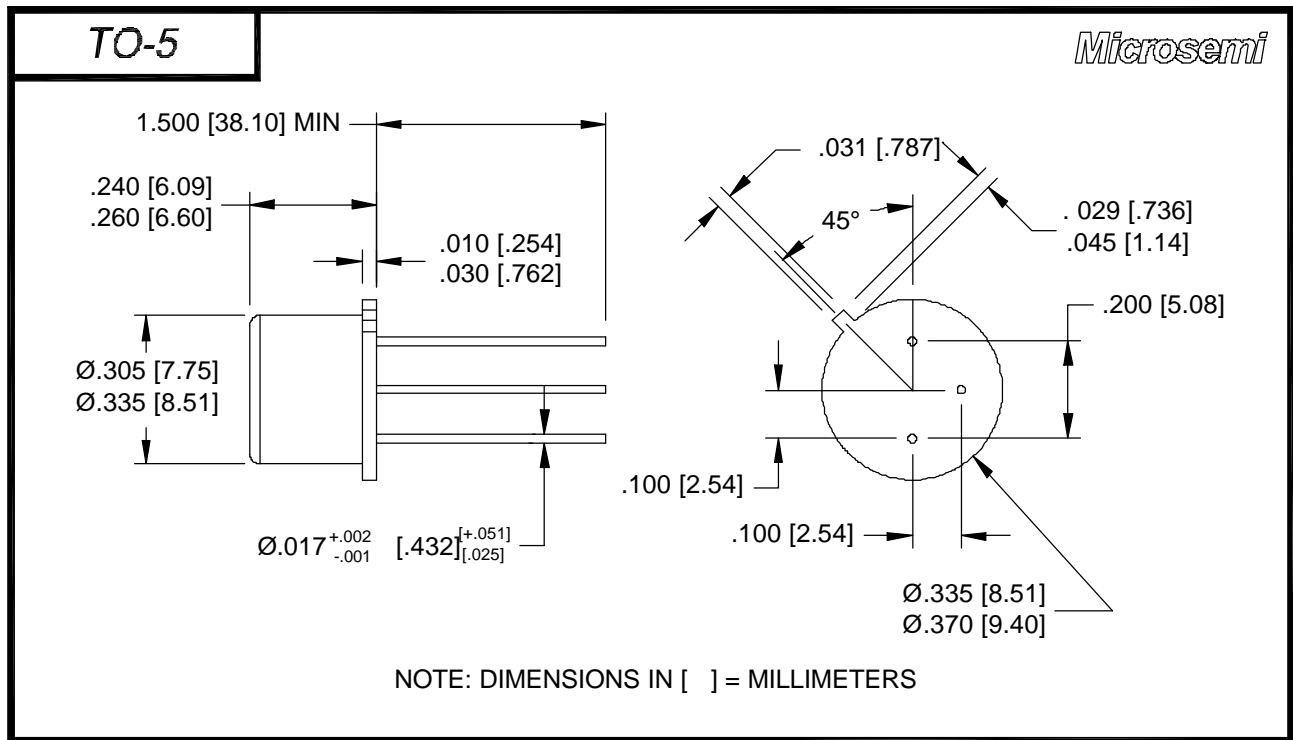
SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VALUE		Units
			Min.	Max.	
$V_{CE(sus)}^*$	Collector-Emitter Sustaining Voltage	$I_C = 20 \text{ mAdc}, I_B = 0$ (Note 1)	40	---	Vdc
$I_{CEX}^*$	Collector Cutoff Current	$V_{CE} = 40 \text{ Vdc}, V_{BE(off)} = 2.0 \text{ Vdc}$ $V_{CE} = 40 \text{ Vdc}, V_{BE(off)} = 2.0 \text{ Vdc}, T_C = 150^\circ\text{C}$	---	10 1.0	$\mu\text{Adc}$ mAdc
$I_{CBO}^*$	Collector Cutoff Current	$V_{CB} = 40 \text{ Vdc}, I_E = 0$	---	10	$\mu\text{Adc}$
$I_{EBO}^*$	Emitter Cutoff Current	$V_{BE} = 4.0 \text{ Vdc}, I_C = 0$	---	1.0	mAdc
$h_{FE}^*$	DC Current Gain (Note 1)	$I_C = 500 \text{ mAdc}, V_{CE} = 1.5 \text{ Vdc}$ $I_C = 1.0 \text{ Adc}, V_{CE} = 1.5 \text{ Vdc}$ $I_C = 1.0 \text{ Adc}, V_{CE} = 1.5 \text{ Vdc}, T_C = -40^\circ\text{C}$	20 25 15	--- 180 ---	--- --- ---
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage (Note 1)	$I_C = 1.0 \text{ Adc}, I_B = 100 \text{ mAdc}, T_C = -40^\circ\text{C to } +100^\circ\text{C}$ $I_C = 3.0 \text{ Adc}, I_B = 300 \text{ mAdc}, T_C = -40^\circ\text{C to } +100^\circ\text{C}$	---	0.75 1.5	Vdc Vdc
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage (Note 1)	$I_C = 1.0 \text{ Adc}, I_B = 100 \text{ mAdc}, T_C = -40^\circ\text{C to } +100^\circ\text{C}$ $I_C = 3.0 \text{ Adc}, I_B = 300 \text{ mAdc}, T_C = -40^\circ\text{C to } +100^\circ\text{C}$	---	1.5 2.3	Vdc Vdc
$f_T^*$	Current-Gain Bandwidth Product (Note 2)	$I_C = 500 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f_{test} = 30 \text{ MHz}$	60	---	MHz
$C_{ob}^*$	Output Capacitance	$V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 0.1 \text{ MHz}$	---	120	pF
$C_{ib}^*$	Input Capacitance	$V_{EB} = 0.5 \text{ Vdc}, I_C = 0, f = 0.1 \text{ MHz}$	---	1000	pF
$t_{on}^*$	Turn-on Time	$V_{CC} = 12 \text{ Vdc}, V_{BE(off)} = 0, I_C = 1.0 \text{ Adc}, I_{B1} = 0.1 \text{ Adc}$	---	100	ns
$t_{off}^*$	Turn-off Time	$V_{CC} = 12 \text{ Vdc}, I_C = 1.0 \text{ Adc}, I_{B1} = I_{B2} = 100 \text{ mAdc}$	---	400	ns

Note 1: Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty Cycle = 2.0%.

Note 2:  $f_T = |h_{fe}| * f_{test}$

\* Indicates JEDEC registered data

PACKAGE MECHANICAL DATA:



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